Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	11	(("20030062614") or ("20030148597") or ("5506753") or ("5909058") or ("6002165") or ("6060774") or ("6184064") or ("6208521") or ("6225695") or ("6297548") or ("6433418")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/04/24 15:27
S2	19761	((438/612,109) or (257/688,691,693, 723,737,780,696,727,686,712,666)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/04/04 09:57
S3	14516	S2 and @pd<"20030330"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 09:57
S4	336	S3 and (stacked adj (die or dice or chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:07
S5	61	S4 and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:07
S6	5	S5 and ("active circuity" or "flash memory array" or "logic circuitry")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:08
S7	2034	(stacked adj (die or dice or chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:07
S8	336	S7 and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:49
S9	. 10	S8 and ("active circuity" or "flash memory array" or "logic circuitry")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 10:37

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S10	393	S7 and (spacer or "support structure")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:48
S11	·76	S7 and ("support structure")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:49
S12	55	S7 and (spacer near5 silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:50
S13	8	S7 and ("support structure" near5 silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/04 10:49
S14	1	("2003/0111716").URPN.	USPAT	OR	ON	2006/04/04 11:09
S15	348	"bonding pad" near size	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:31
S16	21	S15 and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:10
S17	0	"bonding pad" near "1mm"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:30
S18	0	"bonding pad" near "1 mm"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:30
S19	0	"bonding pad" near "1000 micron"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:51

S20	0	"bonding pad" near "die edge"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:31
S21	1014	"bonding pad" near5 size	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:31
S22	288	"bonding pad" adj3 size	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:39
S23	0	"bonding pad" near "300 micrometer"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 13:51
S24	1	10/790907	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/21 15:37
S25	19840	((438/612,109) or (257/688,691,693, 723,737,780,696,727,686,712,666)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/04/24 10:37
S26	14516	S25 and @pd<"20030330"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 10:37
S27	336	S26 and (stacked adj (die or dice or chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON.	2006/04/24 10:37
S28	0	S27 and "flash memory array"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 10:37
S29	32	S27 and "flash memory"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 10:38

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S30	2	S25 and ((buss same memory) same (electronic adj system))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 11:14
S31	43522	(electronic adj system)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 11:14
S32	27	S31 and (memory near5 (coupled or attached) near5 buss)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 11:17
S33	1	S31 and ((flash adj memory) near5 (coupled or attached) near5 buss)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 11:18
S34	3673	S31 and ((flash adj memory))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:11
S35	9	S34 and ((coupled or attached) near5 buss)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR.	ON	2006/04/24 11:21
S36	1579	S31 and (buss)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 11:20
S37	10	S36 and ((flash adj memory) near10 (coupled or attached))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 11:21
S38	1	("6493861").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/04/24 15:28
S39	19840	((438/612,109) or (257/688,691,693, 723,737,780,696,727,686,712,666)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/04/24 15:40

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S40	14516	S39 and @pd<"20030330"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 15:40
S41	. 336	S40 and (stacked adj (die or dice or chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 15:41
S42	336	S41 and (dummy (chip or die))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 15:41
S43	7	S41 and (dummy adj (chip or die))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 15:41
S44	87173	((flash adj memory))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:12
S45	44797	S44 and (bus or buss)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:12
S46	16742	S44 and (coupled adj3 (bus or buss)) .	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:12
S47	679	S46 and "electronic system"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:30
S48	111	S47 and "semiconductor device"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:31
S49	4	S48 and (electrically adj connected)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:13

S50	41	S48 and @pd<"20040329"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:31
S51	43522	"electronic system"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:30
S52	1074	S51 and (memory near5 (coupled adj3 (bus or buss)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:30
S53	137	S52 and "semiconductor device"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:31
S54	71	S53 and @pd<"20040329"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 16:31